## FDC5612

May 1999

## FAIRCHILD

SEMICONDUCTOR IM

## FDC5612 60V N-Channel PowerTrench<sup>™</sup> MOSFET

## **General Description**

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable  $R_{\rm DS(ON)}$  specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

## Features

- 4.3 A, 60 V.  $R_{DS(ON)} = 0.055$  W @  $V_{GS} = 10$  V  $R_{DS(ON)} = 0.064$  W @  $V_{GS} = 6$  V.
- Low gate charge (12.5nC typical).
- Fast switching speed.

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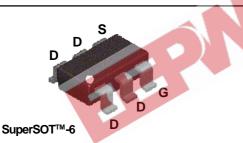
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- High performance trench technology for extremely low R<sub>DS(ON)</sub>.
- SuperSOT<sup>™</sup>-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).

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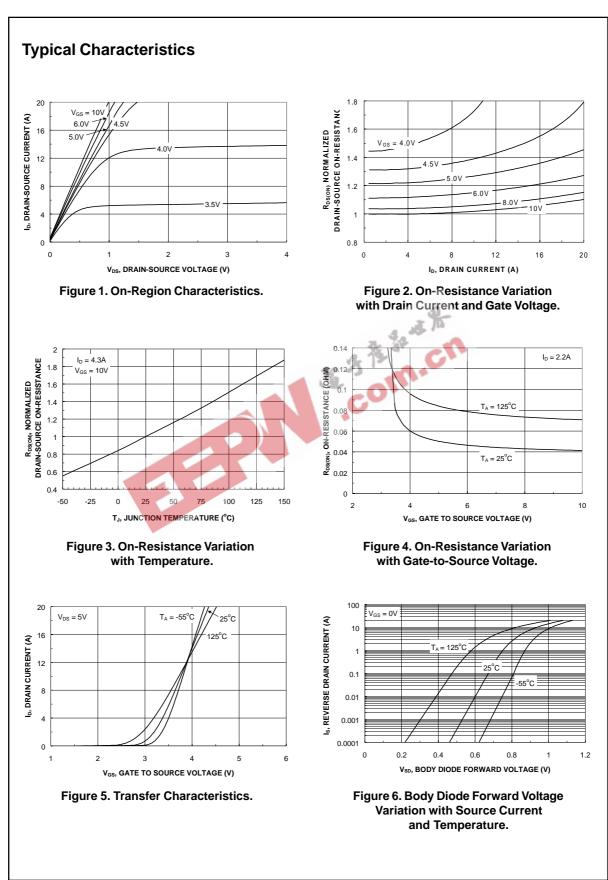


Symbol	Parameter		Ratings	Units	
V <sub>DSS</sub>	Drain-Source Voltage	urce Voltage		V	
V <sub>GSS</sub>	Gate-Source Voltage		<u>+</u> 20	V	
D	Drain Current - Continuous	(Note 1a)	4.3	А	
	Drain Current - Pulsed		20		
PD	Power Dissipation for Single Operation	(Note 1a)	1.6	W	
		(Note 1b)	0.8		
ΓJ, T <sub>stq</sub>	Operating and Storage Junction Temperat	ure Range	-55 to +150	۰C	
<mark>Therma</mark> <sub>Rөл</sub> а	I Characteristics Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	∘C/W	
ς <sup>θic</sup>	Thermal Resistance, Junction-to-Case	(Note 1)	30 °C/M		
	e Outlines and Ordering Info	ormation Reel Size	Tape Width	Quantity	

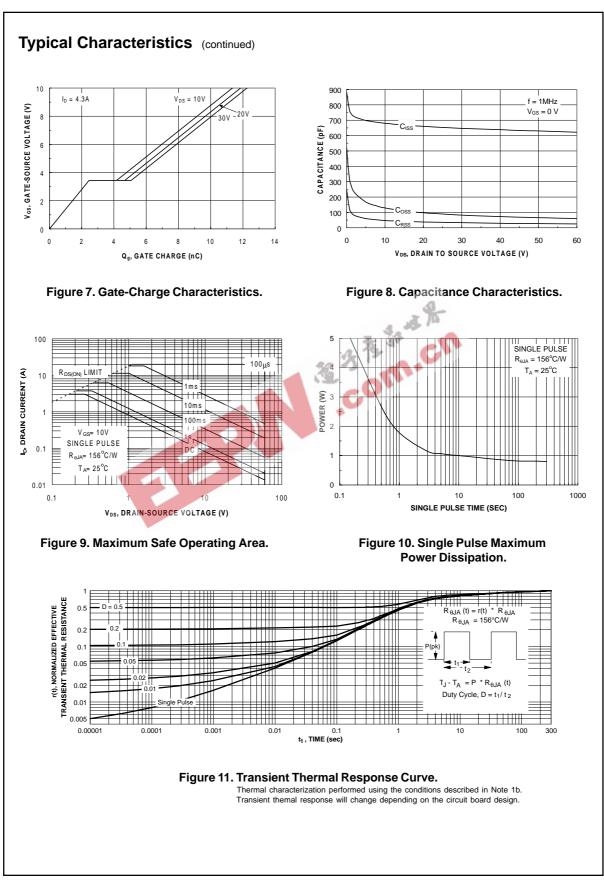
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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics				•	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_D = 250 \mu A$	60			V
$\frac{\Delta BVDSS}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu$ A, Referenced to 25°C		58		mV/∘C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	$V_{GS} = 20 \text{ V},  V_{DS} = 0 \text{ V}$			100	nA
	Gate-Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2	2.2	4	V
$\frac{\Delta VGS(th)}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu$ A, Referenced to 25°C		-5.5		mV/∘C
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 V, I_D = 4.3 A$ $V_{GS} = 10 V, I_D = 4.3 A, T_J = 125 \circ C$ $V_{GS} = 6 V, I_D = 4 A$		0.042 0.072 0.048	0.055 0.094 0.064	Ω
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$	10			Α
<b>g</b> fs	Forward Transconductance	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 4.3 \text{ A}$	-	14		S
Dynamic	Characteristics	2 7 12				
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 V, V_{GS} = 0 V,$		650		pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		80		pF
Crss	Reverse Transfer Capacitance			35		pF
Switchin	g Characteristics (Note 2)					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 30 \text{ V}, \text{ I}_{D} = 1 \text{ A},$		11	20	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, \text{ R}_{GEN} = 6 \Omega$		8	18	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	1		19	35	ns
t <sub>f</sub>	Turn-Off Fall Time	1		6	15	ns
Q <sub>g</sub>	Total Gate Charge	$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 4.3 \text{ A},$		12.5	18	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		2.4		nC
Q <sub>gd</sub>	Gate-Drain Charge	1		2.6		nC
Drain-Sc	ource Diode Characteristics an	d Maximum Ratings	-			
l <sub>s</sub>	Maximum Continuous Drain-Source Did				1.3	Α
-	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_S = 1.3 A$ (Note 2)		0.75	1.2	V
of the drain pi	Drain-Source Diode Forward Voltage sum of the junction-to-case and case-to-ambient re- ns. $R_{qJC}$ is guaranteed by design while $R_{qCA}$ is determine when mounted on a 1.0 in <sup>2</sup> pad of 2 oz. copper.	sistance where the case thermal reference is d	efined as	0.75 the solder	1.2 mounting	

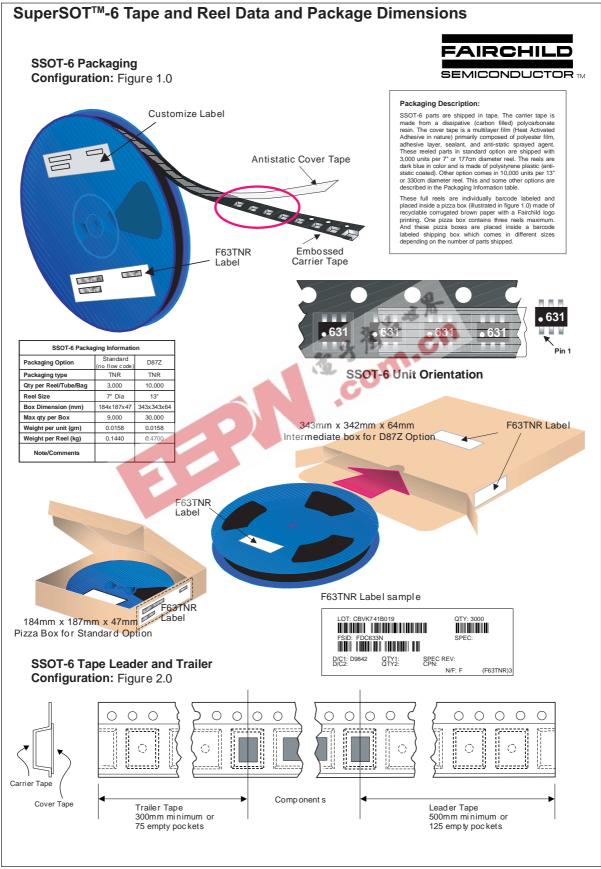
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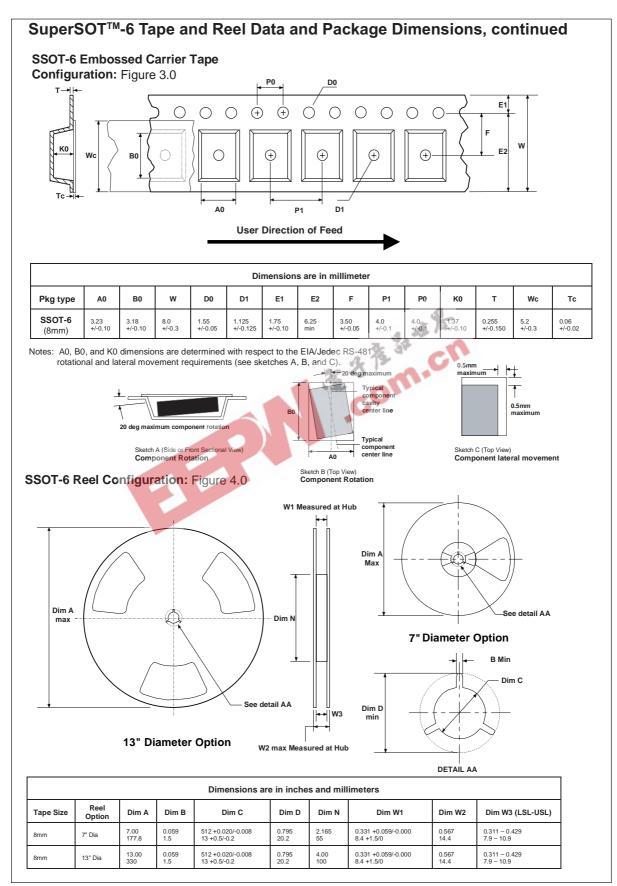
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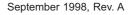


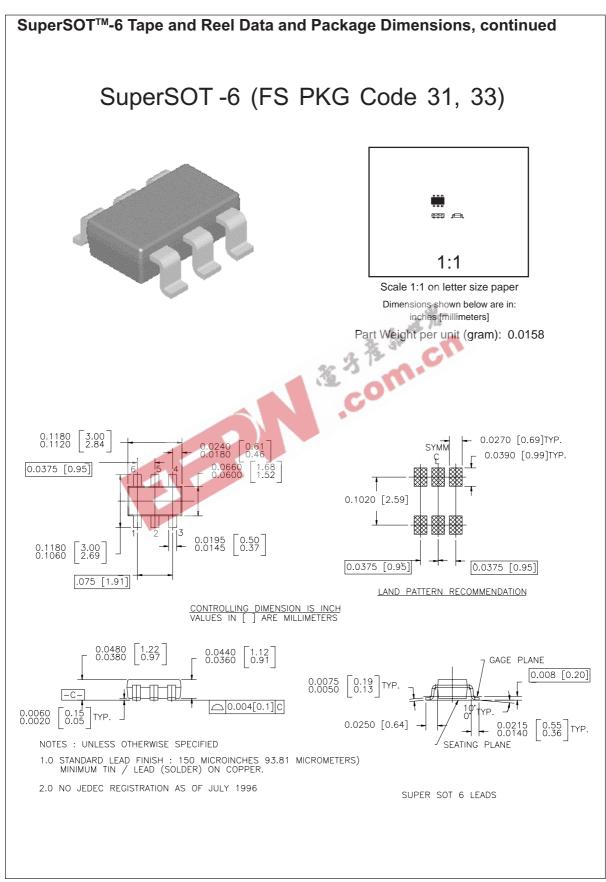




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